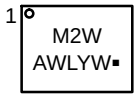
# EEPROM Serial 8-Kb Microwire - Automotive Grade 1, Wettable Flank UDFN Package

# NV93C76WF

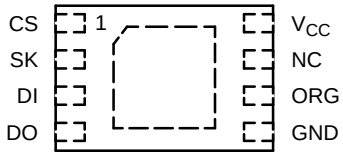

**UDFN8**
**MU SUFFIX**
**CASE 517DH**

### MARKING DIAGRAM




| | |
|---|---|
| M2W | = Specific Device Code |
| A | = Assembly Location |
| WL | = Wafer Lot |
| Y | = Year |
| W | = Work Week |
| ▪ | = Pb−Free Package |

### PIN CONFIGURATION




UDFN−8

### PIN FUNCTION

| Pin Name | Function |
|---|---|
| CS | Chip Select |
| SK | Serial Clock Input |
| DI | Serial Data Input |
| DO | Serial Data Output |
| $V_{CC}$ | Power Supply |
| GND | Ground |
| ORG | Memory Organization |
| NC | No Connection |

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 8 of this data sheet.

### Description

The NV93C76WF is an EEPROM Serial 8−Kb Microwire Automotive Grade 1 device, which is configured as either registers of 16 bits (ORG pin at $V_{CC}$ or Not Connected) or 8 bits (ORG pin at GND) in a Wettable Flank UDFN Package. Each register can be written (or read) serially by using the DI (or DO) pin. The NV93C76 is manufactured using **onsemi**'s advanced CMOS EEPROM floating gate technology. The device is designed to endure 1,000,000 program/erase cycles and has a data retention of 100 years. The device is available in 8−pin UDFN package.

### Features

- Automotive AEC−Q100 Grade 1 (−40°C to +125°C) Qualified
- High Speed Operation: 2 MHz
- 2.5 V to 5.5 V Supply Voltage Range
- Selectable x8 or x16 Memory Organization
- Self−timed Write Cycle with Auto−clear
- Software Write Protection
- Power−up Inadvertant Write Protection
- Low Power CMOS Technology
- 1,000,000 Program/Erase Cycles
- 100 Year Data Retention
- Sequential Read
- UDFN−8 Wettable Flank Package
- This Device is Pb−Free, Halogen Free/BFR Free and RoHS Compliant†

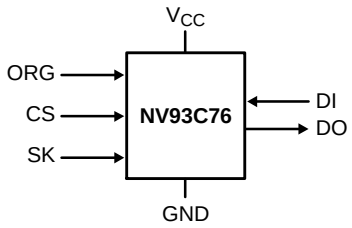



**Figure 1. Functional Symbol**

**Note:** When the ORG pin is connected to $V_{CC}$, the x16 organization is selected. When it is connected to ground, the x8 organization is selected. If the ORG pin is left unconnected, then an internal pull−up device will select the x16 organization.

†For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**Table 1. ABSOLUTE MAXIMUM RATINGS**

| Parameters | Ratings | Units |
|---|---|---|
| Storage Temperature | −65 to +150 | °C |
| Voltage on any Pin with Respect to Ground (Note 1) | −0.5 to +6.5 | V |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The minimum DC input voltage is −0.5 V. During transitions, inputs may undershoot to −2.0 V for periods of less than 20 ns. Maximum DC voltage on output pins is $V_{CC}$ +0.5 V, which may overshoot to $V_{CC}$ +2.0 V for periods of less than 20 ns.

**Table 2. RELIABILITY CHARACTERISTICS** (Note 2)

| Symbol | Parameter | Min | Units |
|---|---|---|---|
| $N_{END}$ (Note 3) | Endurance | 1,000,000 | Program / Erase Cycles |
| $T_{DR}$ | Data Retention | 100 | Years |

2. These parameters are tested initially and after a design or process change that affects the parameter according to appropriate AEC−Q100 and JEDEC test methods.
3. Block Mode, $V_{CC}$ = 5 V, 25°C

**Table 3. D.C. OPERATING CHARACTERISTICS** ($V_{CC}$ = +2.5 V to +5.5 V, $T_A$ = −40°C to +125°C, unless otherwise specified.)

| Symbol | Parameter | Test Conditions | Min | Max | Units |
|---|---|---|---|---|---|
| $I_{CC1}$ | Supply Current (Write) | Write, $V_{CC}$ = 5.0 V | | 2 | mA |
| $I_{CC2}$ | Supply Current (Read) | Read, DO open, $f_{SK}$ = 2 MHz, $V_{CC}$ = 5.0 V | | 500 | μA |
| $I_{SB1}$ | Standby Current (x8 Mode) | $V_{IN}$ = GND or $V_{CC}$<br>CS = GND, ORG = GND | | 5 | μA |
| $I_{SB2}$ | Standby Current (x16 Mode) | $V_{IN}$ = GND or $V_{CC}$<br>CS = GND,<br>ORG = Float or $V_{CC}$ | | 3 | μA |
| $I_{LI}$ | Input Leakage Current | $V_{IN}$ = GND to $V_{CC}$ | | 2 | μA |
| $I_{LO}$ | Output Leakage Current | $V_{OUT}$ = GND to $V_{CC}$<br>CS = GND | | 2 | μA |
| $V_{IL1}$ | Input Low Voltage | 4.5 V ≤ $V_{CC}$ < 5.5 V | −0.1 | 0.8 | V |
| $V_{IH1}$ | Input High Voltage | 4.5 V ≤ $V_{CC}$ < 5.5 V | 2 | $V_{CC}$ + 1 | V |
| $V_{IL2}$ | Input Low Voltage | 2.5 V ≤ $V_{CC}$ < 4.5 V | 0 | $V_{CC}$ x 0.2 | V |
| $V_{IH2}$ | Input High Voltage | 2.5 V ≤ $V_{CC}$ < 4.5 V | $V_{CC}$ x 0.7 | $V_{CC}$ + 1 | V |
| $V_{OL1}$ | Output Low Voltage | 4.5 V ≤ $V_{CC}$ < 5.5 V, $I_{OL}$ = 3 mA | | 0.4 | V |
| $V_{OH1}$ | Output High Voltage | 4.5 V ≤ $V_{CC}$ < 5.5 V, $I_{OH}$ = −400 μA | 2.4 | | V |
| $V_{OL2}$ | Output Low Voltage | 2.5 V ≤ $V_{CC}$ < 4.5 V, $I_{OL}$ = 1 mA | | 0.2 | V |
| $V_{OH2}$ | Output High Voltage | 2.5 V ≤ $V_{CC}$ < 4.5 V, $I_{OH}$ = −100 μA | $V_{CC}$ − 0.2 | | V |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

**Table 4. PIN CAPACITANCE** (Note 4)

| Symbol | Test | Conditions | Min | Typ | Max | Units |
|---|---|---|---|---|---|---|
| $C_{OUT}$ | Output Capacitance (DO) | $V_{OUT}$ = 0 V | | | 5 | pF |
| $C_{IN}$ | Input Capacitance (CS, SK, DI, ORG) | $V_{IN}$ = 0 V | | | 5 | pF |

4. These parameters are tested initially and after a design or process change that affects the parameter.

**Table 5. POWER−UP TIMING** (Notes 6, 5)

| Symbol | Parameter | Max | Units |
|---|---|---|---|
| $t_{PUR}$ | Power−up to Read Operation | 1 | ms |
| $t_{PUW}$ | Power−up to Write Operation | 1 | ms |

5. $t_{PUR}$ and $t_{PUW}$ are the delays required from the time $V_{CC}$ is stable until the specified operation can be initiated.

**Table 6. A.C. TEST CONDITIONS**

| | | |
|---|---|---|
| Input Rise and Fall Times | ≤ 50 ns | |
| Input Pulse Voltages | 0.4 V to 2.4 V | 4.5 V ≤ $V_{CC}$ ≤ 5.5 V |
| Timing Reference Voltages | 0.8 V, 2.0 V | 4.5 V ≤ $V_{CC}$ ≤ 5.5 V |
| Input Pulse Voltages | 0.2 $V_{CC}$ to 0.7 $V_{CC}$ | 2.5 V ≤ $V_{CC}$ ≤ 4.5 V |
| Timing Reference Voltages | 0.5 $V_{CC}$ | 2.5 V ≤ $V_{CC}$ ≤ 4.5 V |
| Output Load | Current Source $I_{OLmax}/I_{OHmax}$; CL = 100 pF | |

**Table 7. A.C. CHARACTERISTICS** ($V_{CC}$ = +2.5 V to +5.5 V, $T_A$ = −40°C to +125°C, unless otherwise specified.)

| Symbol | Parameter | Min | Max | Units |
|---|---|---|---|---|
| $t_{CSS}$ | CS Setup Time | 50 | | ns |
| $t_{CSH}$ | CS Hold Time | 0 | | ns |
| $t_{DIS}$ | DI Setup Time | 100 | | ns |
| $t_{DIH}$ | DI Hold Time | 100 | | ns |
| $t_{PD1}$ | Output Delay to 1 | | 0.25 | μs |
| $t_{PD0}$ | Output Delay to 0 | | 0.25 | μs |
| $t_{HZ}$ (Note 6) | Output Delay to High−Z | | 100 | ns |
| $t_{EW}$ | Program/Erase Pulse Width | | 5 | ms |
| $t_{CSMIN}$ | Minimum CS Low Time | 0.25 | | μs |
| $t_{SKHI}$ | Minimum SK High Time | 0.25 | | μs |
| $t_{SKLOW}$ | Minimum SK Low Time | 0.25 | | μs |
| $t_{SV}$ | Output Delay to Status Valid | | 0.25 | μs |
| $SK_{MAX}$ | Maximum Clock Frequency | DC | 2000 | kHz |

6. This parameter is tested initially and after a design or process change that affects the parameter.

**Table 8. INSTRUCTION SET** (Note 7)

| Instruction | Start Bit | Opcode | Address | | Data | | Comments |
|---|---|---|---|---|---|---|---|
| | | | x8 | x16 | x8 | x16 | |
| READ | 1 | 10 | A10−A0 | A9−A0 | | | Read Address AN– A0 |
| ERASE | 1 | 11 | A10−A0 | A9−A0 | | | Clear Address AN– A0 |
| WRITE | 1 | 01 | A10−A0 | A9−A0 | D7−D0 | D15−D0 | Write Address AN– A0 |
| EWEN | 1 | 00 | 11XXXXXXXXX | 11XXXXXXXX | | | Write Enable |
| EWDS | 1 | 00 | 00XXXXXXXXX | 00XXXXXXXX | | | Write Disable |
| ERAL | 1 | 00 | 10XXXXXXXXX | 10XXXXXXXX | | | Clear All Addresses |
| WRAL | 1 | 00 | 01XXXXXXXXX | 01XXXXXXXX | D7−D0 | D15−D0 | Write All Addresses |

7. Address bit A10 for the 1,024x8 org. and A9 for the 512x16 org. are “don’t care” bits, but must be kept at either a “1” or “0” for READ, WRITE and ERASE commands.

## DEVICE OPERATION

The NV93C76 is a 8192−bit nonvolatile memory intended for use with industry standard microprocessors. The NV93C76 can be organized as either registers of 16 bits or 8 bits. When organized as X16, seven 13−bit instructions control the read, write and erase operations of the device. When organized as X8, seven 14−bit instructions control the read, write and erase operations of the device. The NV93C76 operates on a single power supply and will generate on chip, the high voltage required during any write operation.

Instructions, addresses, and write data are clocked into the DI pin on the rising edge of the clock (SK). The DO pin is normally in a high impedance state except when reading data from the device, or when checking the ready/busy status after a write operation.

The ready/busy status can be determined after the start of a write operation by selecting the device (CS high) and polling the DO pin; DO low indicates that the write operation is not completed, while DO high indicates that the device is ready for the next instruction. If necessary, the DO pin may be placed back into a high impedance state during chip select by shifting a dummy “1” into the DI pin. The DO pin will enter the high impedance state on the falling edge of the clock (SK). Placing the DO pin into the high impedance state is recommended in applications where the DI pin and the DO pin are to be tied together to form a common DI/O pin.

The format for all instructions sent to the device is a logical “1” start bit, a 2−bit (or 4−bit) opcode, 10−bit address (an additional bit when organized X8) and for write operations a 16−bit data field (8−bit for X8 organizations). The most significant bit of the address is “don’t care” but it must be present.

### Read

Upon receiving a READ command and an address (clocked into the DI pin), the DO pin of the NV93C76 will come out of the high impedance state and, after sending an initial dummy zero bit, will begin shifting out the data addressed (MSB first). The output data bits will toggle on the rising edge of the SK clock and are stable after the specified time delay ($t_{PD0}$ or $t_{PD1}$).

For the NV93C76, after the initial data word has been shifted out and CS remains asserted with the SK clock continuing to toggle, the device will automatically increment to the next address and shift out the next data word in a sequential READ mode. As long as CS is continuously asserted and SK continues to toggle, the device will keep incrementing to the next address automatically until it reaches the end of the address space, then loops back to address 0. In the sequential READ mode, only the initial data word is preceeded by a dummy zero bit. All subsequent data words will follow without a dummy zero bit.

### Write

After receiving a WRITE command, address and the data, the CS (Chip Select) pin must be deselected for a minimum of $t_{CSMIN}$. The falling edge of CS will start the self clocking clear and data store cycle of the memory location specified in the instruction. The clocking of the SK pin is not necessary after the device has entered the self clocking mode. The ready/busy status of the NV93C76 can be determined by selecting the device and polling the DO pin. Since this device features Auto−Clear before write, it is NOT necessary to erase a memory location before it is written into.

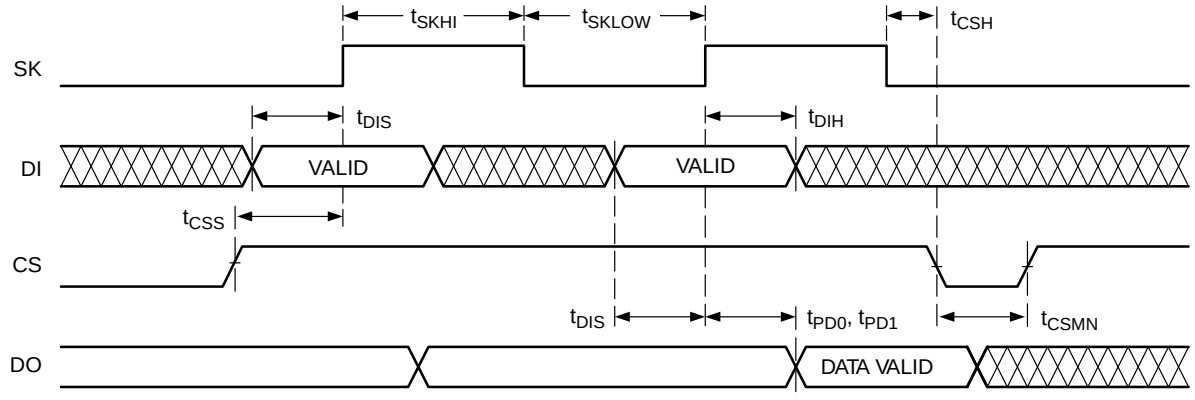



**Figure 2. Synchronous Data Timing**

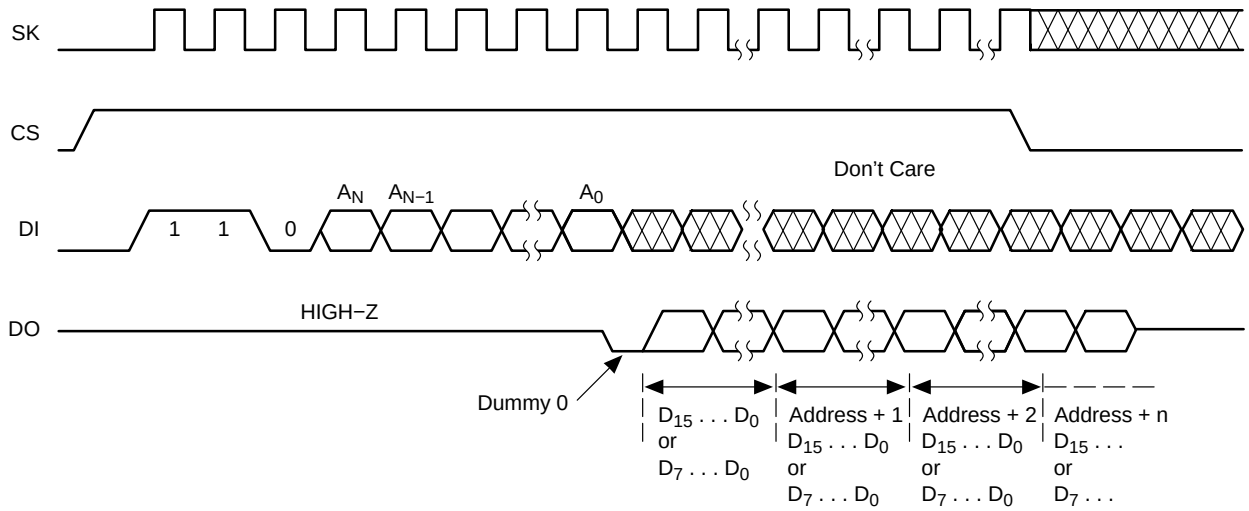



**Figure 3. READ Instruction Timing**

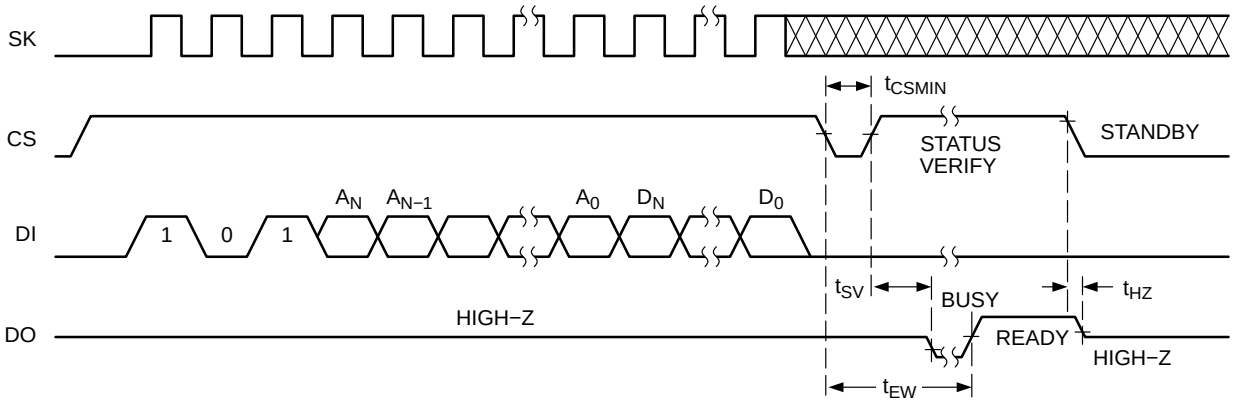



**Figure 4. WRITE Instruction Timing**

### Erase

Upon receiving an ERASE command and address, the CS (Chip Select) pin must be deasserted for a minimum of $t_{CSMIN}$. The falling edge of CS will start the self clocking clear cycle of the selected memory location. The clocking of the SK pin is not necessary after the device has entered the self clocking mode. The ready/busy status of the NV93C76 can be determined by selecting the device and polling the DO pin. Once cleared, the content of a cleared location returns to a logical “1” state.

### Erase/Write Enable and Disable

The NV93C76 powers up in the write disable state. Any writing after power−up or after an EWDS (write disable) instruction must first be preceded by the EWEN (write enable) instruction. Once the write instruction is enabled, it will remain enabled until power to the device is removed, or the EWDS instruction is sent. The EWDS instruction can be used to disable all NV93C76 write and clear instructions, and will prevent any accidental writing or clearing of the device. Data can be read normally from the device regardless of the write enable/disable status.

### Erase All

Upon receiving an ERAL command, the CS (Chip Select) pin must be deselected for a minimum of $t_{CSMIN}$. The falling edge of CS will start the self clocking clear cycle of all memory locations in the device. The clocking of the SK pin is not necessary after the device has entered the self clocking mode. The ready/busy status of the NV93C76 can be determined by selecting the device and polling the DO pin. Once cleared, the contents of all memory bits return to a logical “1” state.

### Write All

Upon receiving a WRAL command and data, the CS (Chip Select) pin must be deselected for a minimum of $t_{CSMIN}$. The falling edge of CS will start the self clocking data write to all memory locations in the device. The clocking of the SK pin is not necessary after the device has entered the self clocking mode. The ready/busy status of the NV93C76 can be determined by selecting the device and polling the DO pin. It is not necessary for all memory locations to be cleared before the WRAL command is executed.

***Note 1:*** *After the last data bit has been sampled, Chip Select (CS) must be brought Low before the next rising edge of the clock (SK) in order to start the self−timed high voltage cycle. This is important because if CS is brought low before or after this specific frame window, the addressed location will not be programmed or erased.*

### Power−On Reset (POR)

The NV93C76 incorporates Power−On Reset (POR) circuitry which protects the device against malfunctioning while $V_{CC}$ is lower than the recommended operating voltage.

The device will power up into a read−only state and will power−down into a reset state when $V_{CC}$ crosses the POR level of ~1.3 V.

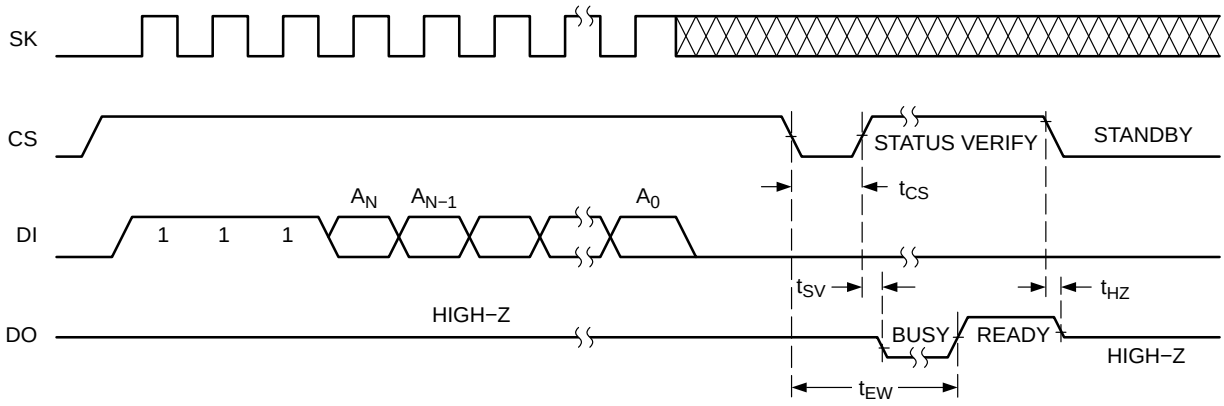



**Figure 5. ERASE Instruction Timing**

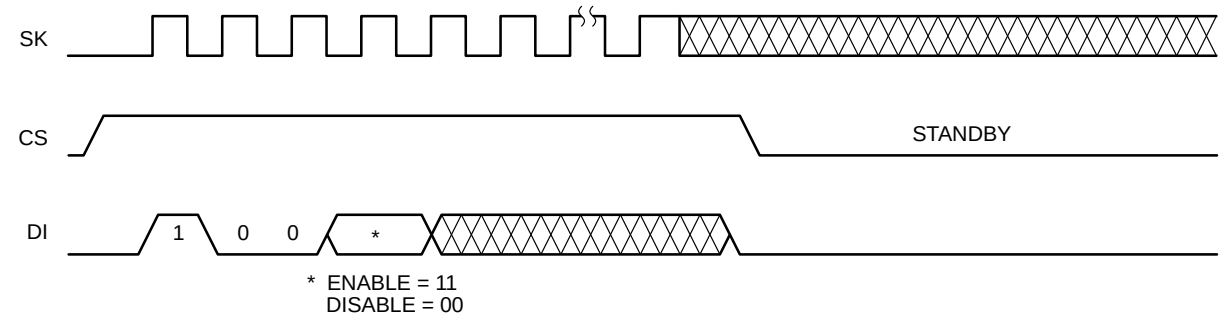



**Figure 6. EWEN/EWDS Instruction Timing**

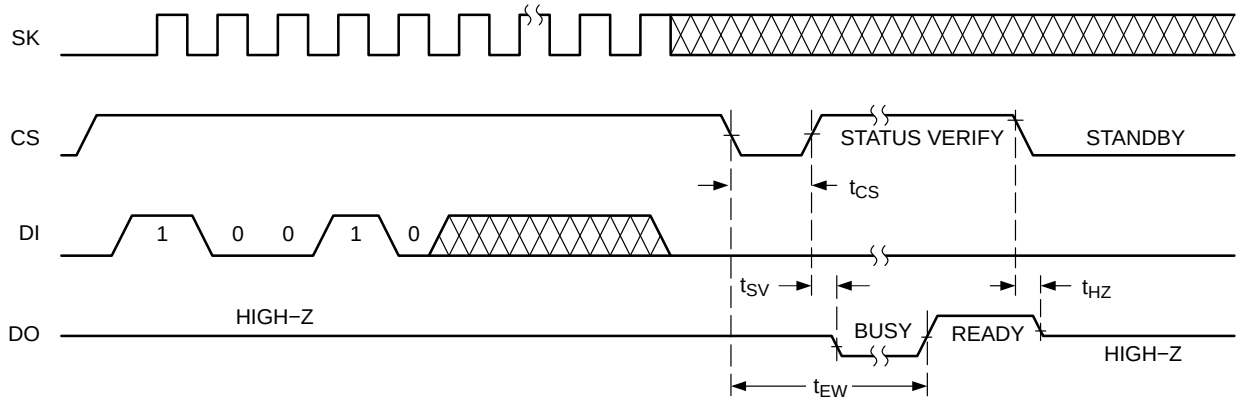



**Figure 7. ERAL Instruction Timing**

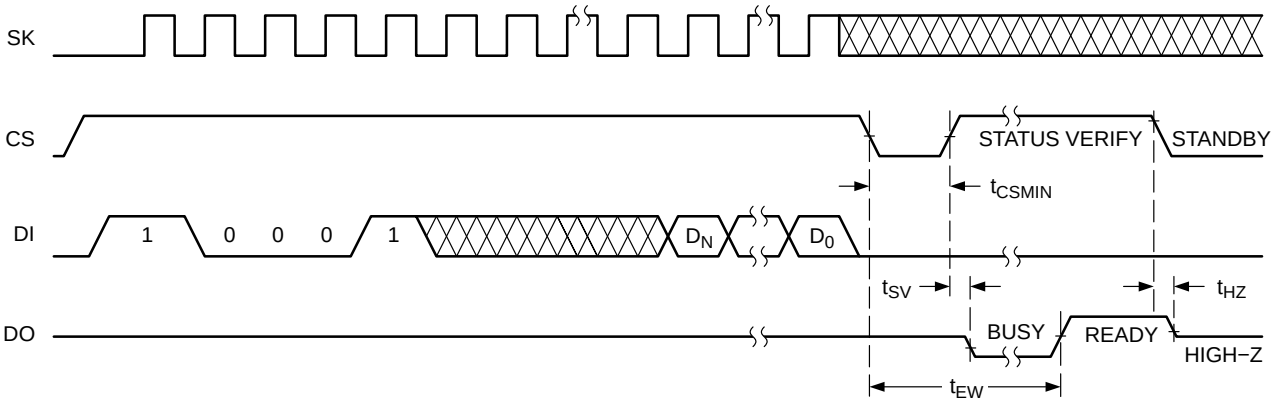



**Figure 8. WRAL Instruction Timing**

## ORDERING INFORMATION

| Device Order Number | Specific Device Marking | Package Type | Temperature Range | Shipping† |
|---|---|---|---|---|
| NV93C76BMUW3VTBG | M2W | UDFN−8 (2x3 mm) Wettable Flank | V = Auto Grade 1 (−40°C to +125°C) | Tape & Reel, 3,000 Units / Reel |

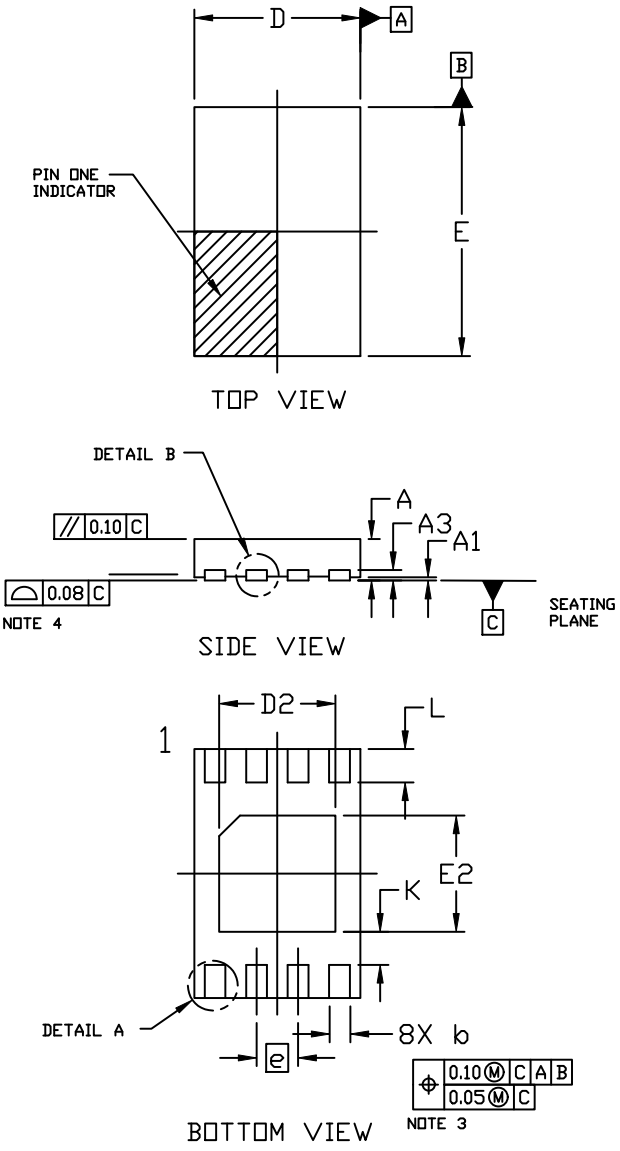
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

8. All packages are RoHS−compliant (Lead−free, Halogen−free).
9. The standard lead finish is NiPdAu.
10. For additional package and temperature options, please contact your nearest **onsemi** sales office.
11. For detailed information and a breakdown of device nomenclature and numbering systems, please see the **onsemi** Device Nomenclature document, TND310/D, available at www.onsemi.com

**UDFN8 2x3, 0.5P**
CASE 517DH
ISSUE A

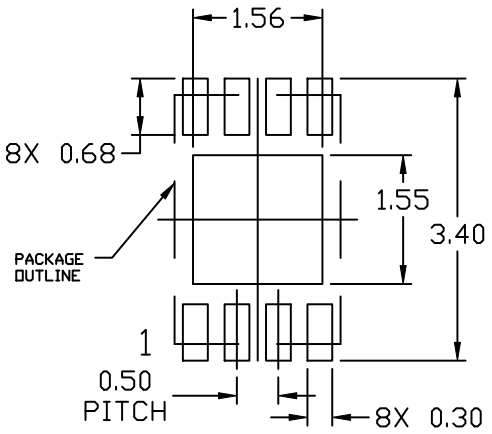
**SCALE 2:1**

DATE 10 DEC 2020




NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.25MM FROM THE TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

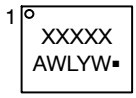
| | MILLIMETERS | | |
|---|---|---|---|
| DIM | MIN. | NOM. | MAX. |
| A | 0.45 | 0.50 | 0.55 |
| A1 | 0.00 | --- | 0.05 |
| A3 | 0.13 REF | | |
| b | 0.20 | 0.25 | 0.30 |
| D | 1.90 | 2.00 | 2.10 |
| D2 | 1.30 | 1.40 | 1.50 |
| E | 2.90 | 3.00 | 3.10 |
| E2 | 1.30 | 1.40 | 1.50 |
| e | 0.50 BSC | | |
| K | 0.40 REF | | |
| L | 0.30 | 0.40 | 0.50 |




RECOMMENDED MOUNTING FOOTPRINT*

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**GENERIC MARKING DIAGRAM***




| | |
|---|---|
| XXXXX | = Specific Device Code |
| A | = Assembly Location |
| WL | = Wafer Lot |
| Y | = Year |
| W | = Work Week |
| ▪ | = Pb−Free Package |

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

| | | |
|---|---|---|
| **DOCUMENT NUMBER:** | **98AON06579G** | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red. |
| **DESCRIPTION:** | **UDFN8 2X3, 0.5P** | **PAGE 1 OF 1** |

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